



HAOPIN MICROELECTRONICS CO.,LTD.

Description

Glass passivated, sensitive gate thyristors in a plastic envelope, intended for use in general purpose switching and phase control applications. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

Symbol		Simplified outline	
			
Pin	Description		
1	Cathode		
2	Anode		
3	Gate		

Applications:

- ◆ Motor control
- ◆ Industrial and domestic lighting
- ◆ Heating
- ◆ Static switching

Features

- ◆ Blocking voltage to 800 V
- ◆ On-state RMS current to 8 A
- ◆ Ultra low gate trigger current

SYMBOL	PARAMETER	Value	Unit
V_{DRM}	Repetitive peak off-state voltages	500R	V
V_{RRM}	Voltages	600R	
		800R	
$I_T (RMS)$	RMS on-state current	8	A
I_{TSM}	Non-repetitive peak on-state current	75	A

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
$R_{th j-mb}$	Thermal resistance Junction to mounting base		-	-	2.0	K/W
$R_{th j-a}$	Thermal resistance Junction to ambient	In free air	-	60	-	K/W

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Limiting values in accordance with the Maximum system(IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V_{DRM} V_{RRM}	Repetitive peak off-state Voltages	500R 600R 800R	-	500 600 800	V
I_{TAV}	Average on-state current	Half sine wave; $T_{mb} \leq 111^\circ C$	-	5	A
$I_{T(RMS)}$	RMS on-state current	All conduction angles	-	8	A
I_{TSM}	Non-repetitive peak On-state current	half sine wave; $T_j = 25^\circ C$ prior to surge	T=10ms	75	A
			T=8.3ms	82	A
I^2t	I^2t for fusing	T=10ms	-	28	A ² S
DI_T/dt	Repetitive rate of rise of on-state current after trigering	$I_{TM}=10A$; $I_G=50mA$; $DIG/dt=50mA/\mu s$	-	50	A/ μs
I_{GM}	Peak gate current		-	2	A
V_{GM}	Peak gate voltage		-	5	V
P_{GM}	Peak gate power		-	5	W
$P_{G(AV)}$	Average gate power	Over any 20 ms period	-	0.5	W
T_{stg}	Storage temperature		-40	150	$^\circ C$
T_j	Operating junction Temperature		-	125 ²	$^\circ C$

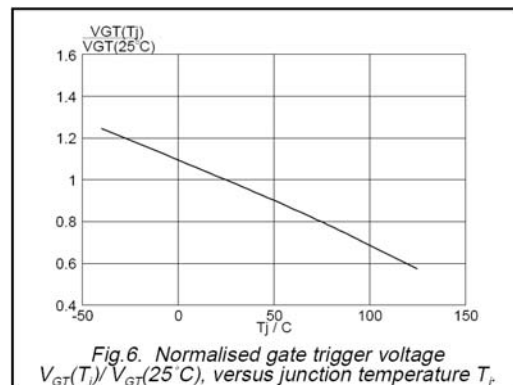
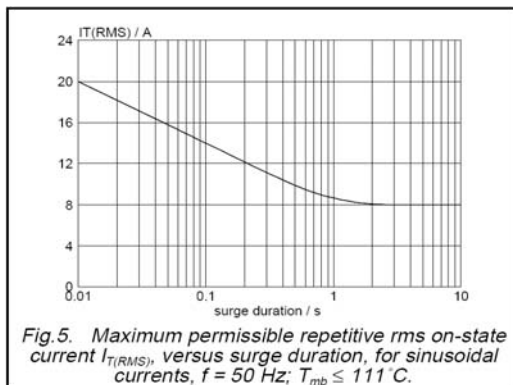
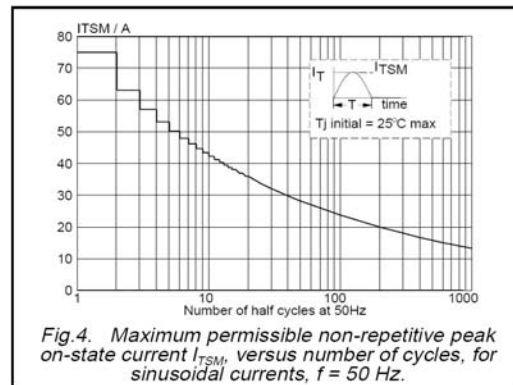
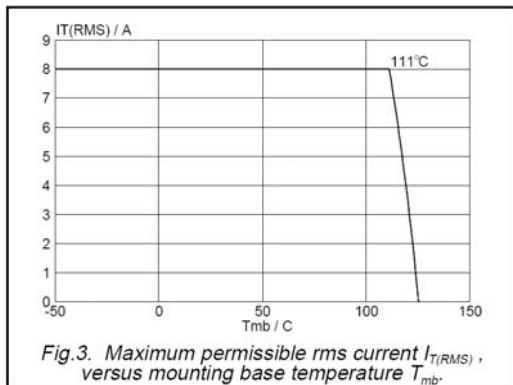
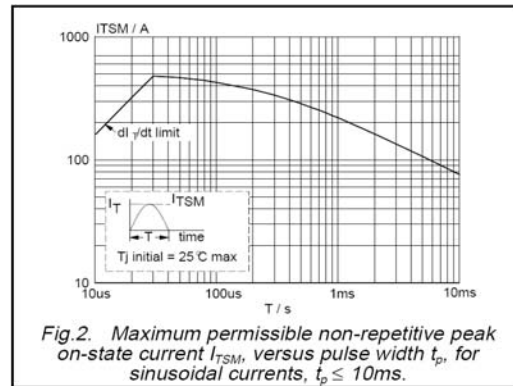
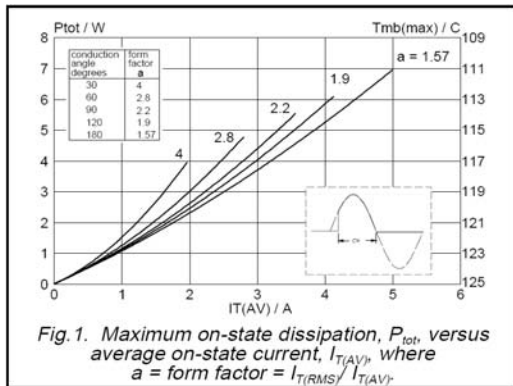
$T_j=25^\circ C$ unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
Static characteristics						
I_{GT}	Gate trigger current	$V_D=12V$; $I_T=0.1A$	-	50	200	μA
I_L	Latching current	$V_D=12V$; $I_{GT}=0.1A$	-	0.4	10	mA
I_H	Holding current	$V_D=12V$; $I_{GT}=0.1A$	-	0.3	6	mA
V_T	On-state voltage	$I_T=16A$	-	1.3	1.5	V
V_{GT}	Gate trigger voltage	$V_D=12V$; $I_T=0.1A$	-	0.4	1.5	V
		$V_D=V_{DRM(max)}$; $I_T=0.1A$; $T_j=110^\circ C$	0.1	0.2	-	V
$I_D I_R$	Off-state leakage current	$V_D=V_{DRM(max)}$; $V_R=V_{RRM(max)}$; $T_j=125^\circ C$	-	0.1	0.5	mA

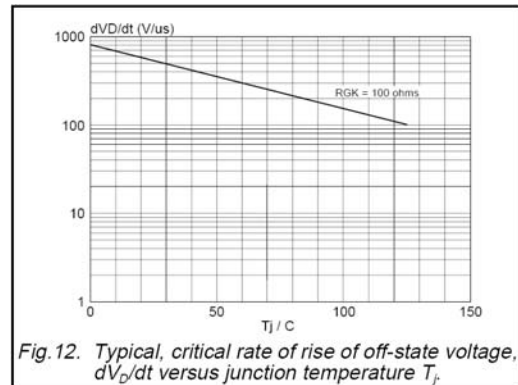
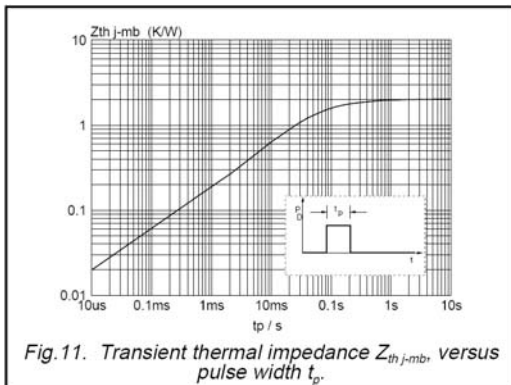
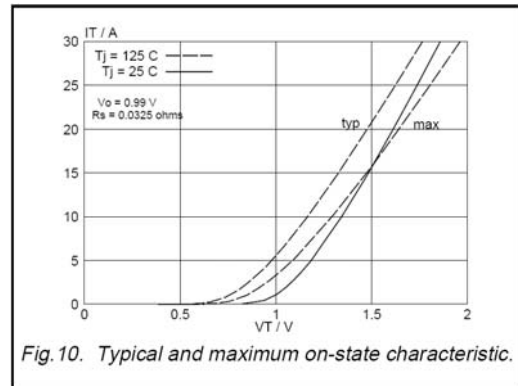
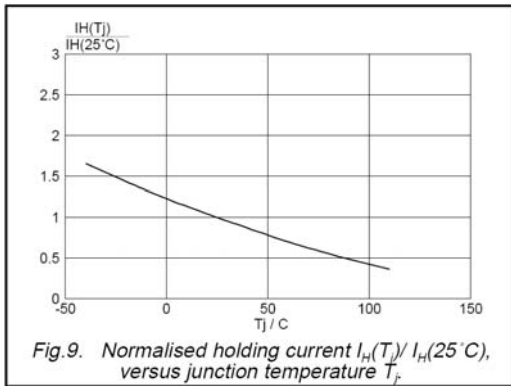
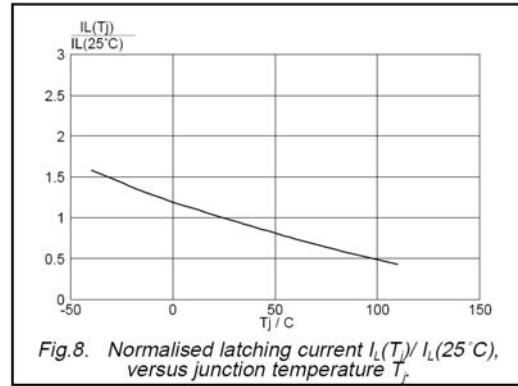
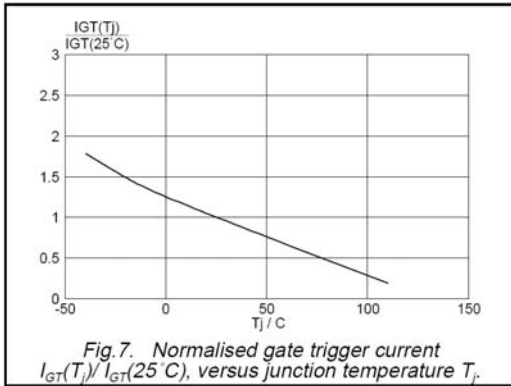
Dynamic Characteristics

D_{VD}/dt	Critical rate of rise of Off-state voltage	$V_{DM}=67\% V_{DRM(max)}$; $T_j=125^\circ C$; Exponential wave form; $R_{GK}=100\ \Omega$	50	100	-	V/ μs
t_{gt}	Gate controlled turn-on time	$I_{TM}=10A$; $V_D=V_{DRM(max)}$; $I_G=5mA$; $DI_G/dt=0.2A/\mu s$	-	2	-	μs
t_g	Crcuit commutated tum- off time	$V_{DM}=67\% V_{DRM(max)}$; $T_j=125^\circ C$; $I_{TM}=12A$ $V_R=24V$; $dI_{TM}/dt=10A/\mu s$ $dv_D/dt=2V/\mu s$; $R_{GK}=1k\ \Omega$	-	100	-	μs

Description



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MECHANICAL DATA

